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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/801,374	03/15/2004	Pooran Chandra Joshi	SLA0787	3177

55286 7590 07/21/2006

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EXAMINER
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LEE, HSIEN MING

ART UNIT	PAPER NUMBER
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2823

DATE MAILED: 07/21/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

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JOSHI ET AL.

SLA 0787

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2823

20060718

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**Commissioner for Patents**

This is to replace the examiner's statement of reasons for allowance mailed June 2, 2006. The reasons for allowance should have been written as following:

In re claim 1, the prior art of record neither teaches nor suggests treating the substrate at temperature equal to and less than 360°C, using a high density (HD) source; and forming an M oxide layer overlying the substrate where M is an element selected from a group including elements chemically defined as a solid and having an oxidation state in a range of +2 to +5, excluding silicon.

In re claim 3, the prior art of record neither teaches nor suggests using an inductively coupled plasma (ICP) source for plasma oxidizing the substrate.

In re claims 8 and 17, the prior art of record neither teaches nor suggests forming a transparent substrate layer and forming a diffusion barrier overlying the transparent substrate layer.

In re claim 24, the prior art of record neither teaches nor suggests treating the substrate at temperature equal to and less than 360°C, using a high density (HD) inductively coupled plasma (ICP) source; and forming, overlying a substrate, an M oxide layer where M is selected from a group including elements chemically defined as a solid and having an oxidation state in a range of +2 to +5, excluding silicon.

**HSIEN-MING LEE**  
**PRIMARY EXAMINER**Hsien-ming Lee  
Primary Examiner  
Art Unit: 2823

7/8/06